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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/604,587	07/31/2003	CHING-YU CHANG	10264-US-PA-1	1586	
31561	7590 01/20/200	•	EXAM	INER	
JIANQ CHYUN INTELLECTUAL PROPERTY OFFICE			PERKINS, PAMELA E		
7 FLOOR-1, ROOSEVEI	,  NO. 100 LT ROAD, SECTION 2		ART UNIT	PAPER NUMBER	
TAIPEI, 100 TAIWAN			2822		
			DATE MAILED: 01/20/2004		

Please find below and/or attached an Office communication concerning this application or proceeding.

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		Ap	plication No.	Applicant(s)		
			1/604,587	CHANG, CHING-	YU	
Office Action Summary			aminer	Art Unit		
		1	mela E Perkins	2822		
Period fo	The MAILING DATE of this commu r Reply	nication appears	on the cover sheet wit	h the correspondence a	ddress	
A SHO THE N - Exten after: - If the - If NO - Failur - Any re	A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.  - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.  - If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.  - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.  - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).  - Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).					
1)[🛛	Responsive to communication(s) fi	led on <u>01 Augus</u>	st 2003.			
2a)□	This action is FINAL.	2b)⊠ This actio	on is non-final.			
3)□	Since this application is in condition closed in accordance with the practice.	n for allowance of tice under <i>Ex pa</i>	except for formal matte arte Quayle, 1935 C.D.	ers, prosecution as to the 11, 453 O.G. 213.	e merits is	
Dispositi	on of Claims					
5)□ 6)⊠ 7)□	4) ☐ Claim(s) 1-9 is/are pending in the application. 4a) Of the above claim(s) is/are withdrawn from consideration.  5) ☐ Claim(s) is/are allowed.  6) ☐ Claim(s) 1-9 is/are rejected.  7) ☐ Claim(s) is/are objected to.  8) ☐ Claim(s) are subject to restriction and/or election requirement.					
Applicati	ion Papers	1		·		
10)⊠	The specification is objected to by the drawing(s) filed on <u>01 August 2</u> Applicant may not request that any objected the oath or declaration is objected	2 <u>003</u> is/are: a)∑ ection to the draw ng the correction i	ring(s) be held in abeyand s required if the drawing(	ce. See 37 CFR 1.85(a). s) is objected to. See 37 C	DFR 1.121(d).	
Priority (	under 35 U.S.C. §§ 119 and 120					
a) 13)□ / 3 3 14)⊠ /	Acknowledgment is made of a claimage of the priorical Certified copies of the priorical Certified copies of the priorical Certified copies of the certified copies application from the International Certified detailed Office act Acknowledgment is made of a claimage of the certified copies application from the International Certified Certified Copies and Certified C	ty documents had by documents had be sof the priority tional Bureau (Pation for a list of the for domestic pation in the first sof the for domestic pation is the first sof domestic pation.	ave been received. Ave been received in A documents have been CT Rule 17.2(a)). Ave certified copies not riority under 35 U.S.C. Aventence of the specification has beriority under 35 U.S.C.	pplication No received in this National received. § 119(e) (to a provision ation or in an Application een received. §§ 120 and/or 121 since	nal application) in Data Sheet. se a specific	
2) 🔲 Noti	nt(s) ce of References Cited (PTO-892) ce of Draftsperson's Patent Drawing Review rmation Disclosure Statement(s) (PTO-1449		5) Notice of I	Summary (PTO-413) Paper N nformal Patent Application (P		

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### **DETAILED ACTION**

This office action is in response to the filing of the application papers on 1 August 2003. Claims 1-9 are pending.

# Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1-9 are rejected under 35 U.S.C. 103(a) as being unpatentable over Chang (6,541,828) in view of Ko (6,479,864) and Li et al. (6,545,310).

Chang discloses a method of fabricating a non-volatile memory where a longitudinal strip stacked layer is formed over a substrate (40); forming a buried bit line (46) in the substrate on each side of the longitudinal strip; patterning the longitudinal strip to form a plurality of stacked blocks; forming a dielectric layer (48) over the substrate (40); forming a word line (44) over the dielectric layer (48). Chang further discloses forming the buried bit line using ion implantation with the longitudinal strip as a mask (Fig. 7B; col. 3, line 22 thru col. 4, line 41). Chang does not disclose the longitudinal strip having a cap layer, a conductive layer and gate dielectric layer and the word line connecting blocks on the same row serially.

Ko discloses a method of fabricating a non-volatile memory where a longitudinal strip stacked layer is formed over a substrate (12), wherein the longitudinal strip

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includes a gate dielectric layer (42), a conductive layer (44) and a cap layer (48); and forming a dielectric layer (22) over the substrate (12). Ko further discloses the cap layer (48) having a greater etch rate than the dielectric layer (22). Ko also discloses conducting a wet or dry anisotropic etching process to remove the cap layers (Fig. 5; col. 7, line 36 thru col. 8, line 14).

Since Chang and Ko are both from the same field of endeavor, a method of fabricating a non-volatile memory, the purpose disclosed by Chang would have been recognized in the pertinent art of Ko. Therefore, it would have been obvious to one ordinary skill in the art at the time the invention was made to modify Chang by the longitudinal strip having a cap layer, a conductive layer and gate dielectric layer as taught by Ko to preventing layers not aligned with the selected pattern (col. 7, lines 65-67).

Li et al. disclose a method of fabricating a non-volatile memory where a longitudinal strip stacked layer is formed over a substrate and forming a word line (2) over the substrate to connect blocks on the same row serially (fig. 4; col. 5, lines 3-51).

Since Chang and Li et al. are both from the same field of endeavor, a method of fabricating a non-volatile memory, the purpose disclosed by Li et al. would have been recognized in the pertinent art of Chang. Therefore, it would have been obvious to one ordinary skill in the art at the time the invention was made to modify Chang by the word line connecting blocks on the same row serially as taught by Li et al. to obtain control the gated structures (col. 5, lines 5-30).

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## Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Pamela E Perkins whose telephone number is (571) 272-1840. The examiner can normally be reached on Monday thru Friday, 9:00am to 5:30pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Amir Zarabian can be reached on (571) 272-1852. The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

PEP

a

# Notice of References Cited Application/Control No. 10/604,587 Examiner Pamela E Perkins Applicant(s)/Patent Under Reexamination CHANG, CHING-YU Page 1 of 1

## U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	Α	US-6,479,864	11-2002	Ko, Kei-Yu	257/347
	В	US-6,541,828	04-2003	Chang, Ching-Yu	257/390
	С	US-6,545,310	04-2003	Li et al.	257/314
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	Н	US-			
	1	US-			
	J	US-			
	К	US-			
	7	US-			
	М	US-			

#### **FOREIGN PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
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### **NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).) Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.